

BRF8N80 (CS8N80F)

N-CHANNEL MOSFET/N 沟道 MOS 晶体管

用途：用于高功率 DC/DC 转换和功率开关。

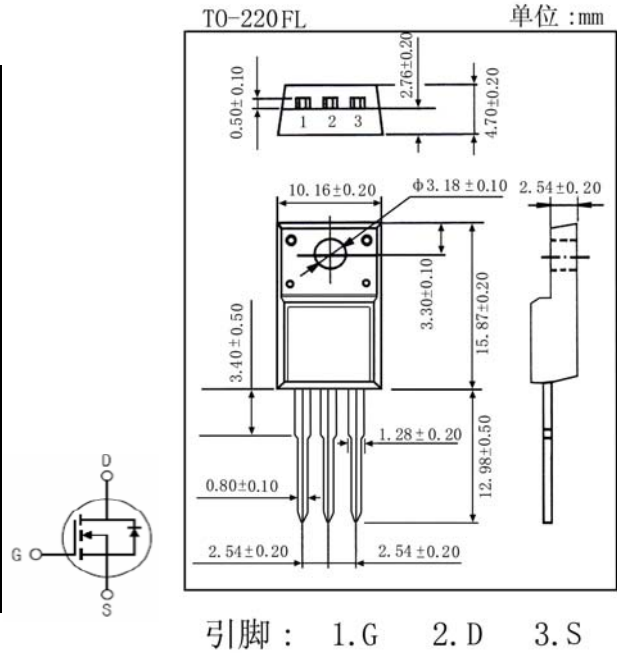
Purpose: These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

特点：低栅电荷, 低反馈电容, 开关速度快。

Features: Low gate charge, low crss, fast switching.

极限参数/Absolute maximum ratings (Ta=25°C)

参数符号 Symbol	数值 Rating	单位 Unit
V _{DSS}	800	V
I _D (Tc=25°C)	8.0	A
I _D (Tc=100°C)	5.4	A
I _{DM}	32	A
V _{GSS}	±30	V
E _{AS}	950	mJ
E _{AR}	85	mJ
I _{AR}	4.1	A
P _D (Tc=25°C)	130	W
T _J , T _{STG}	-55 to 150	°C



电性能参数/Electrical Characteristics (Ta=25°C)

参数符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
BV _{DSS}	V _{GS} =0V I _D =250 μA	800			V
I _{DSS}	V _{DS} =800V V _{GS} =0V			25	μA
	V _{DS} =640V T _a =125°C			250	μA
I _{GSS}	V _{GS} =±30V V _{DS} =0V			±0.1	μA
V _{GS(th)}	V _{DS} =V _{GS} I _D =250 μA	2.0		4.0	V
R _{DS(on)}	V _{GS} =10V I _D =4.0A		1.1	1.25	Ω
g _{FS}	V _{DS} =15V I _D =4.0A		8.5		S
V _{SD}	V _{GS} =0V I _S =8.0A			1.5	V
C _{iss}	V _{DS} =25V V _{GS} =0V f=1.0MHz		2400		pF
C _{oss}		160		pF	
C _{rss}		17		pF	
t _{d(on)}			40		ns
t _r	V _{DD} =400V I _D =8A R _G =4.7Ω V _{GS} =10V		120		ns
t _{d(off)}			70		ns
t _f			80		ns

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